

ABSTRACT OF THE DISCLOSURE

An object of the present invention is to provide a semiconductor apparatus and a method of manufacturing the same, in which dispersion of a threshold voltage  $V_{th}$  of a transistor at every transistor is reduced to remove generation of fixed charges in a gate insulation film and a surface level to stabilize the operation of the semiconductor apparatus. A semiconductor apparatus having a MIS transistor (1), wherein a gate electrode (4) of said MIS transistor (1), which mainly contributes to the operation of a circuit, is continuously formed to a position above a bypass film (8) made of an insulation film through which a leak current is able to easily flow as compared with a gate insulation film (7) of said MIS transistor (1) under the same voltage.